Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

HN1C01F

Audio Frequency General Purpose Amplifier Applications

Small package (Dual type)

High voltage and high current

 $: V_{CEO} = 50V, I_{C} = 150mA (max)$

High h_{FE} : $h_{FE} = 120 \sim 400$

Excellent hfe linearity

 $: h_{FE} (I_C = 0.1 \text{mA}) / h_{FE} (I_C = 2 \text{mA}) = 0.95 \text{ (typ.)}$

Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	Ic	150	mA
Base current	Ι _Β	30	mA
Collector power dissipation	P _C *	300	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Electrical Characteristics (Ta = 25°C) (Q1,Q2 Common)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	V _{CB} = 60V, I _E = 0	_	_	0.1	μA
Emitter cut-off current	I _{EBO}	_	$V_{EB} = 5V, I_{C} = 0$	1		0.1	μA
DC current gain	h _{FE (Note)}	_	V_{CE} = 6V, I_C = 2mA	120		400	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = 100mA, I _B = 10mA	1	0.1	0.25	V
Transition frequency	f _T	_	V _{CE} = 10V, I _C = 1mA	80	_	_	MHz
Collector output capacitance	C _{ob}	_	V _{CB} = 10V, I _E = 0, f = 1MHz	_	2	3.5	pF

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Note: hfe Classification

Y (Y): 120~240, GR (G): 200~400

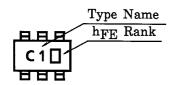
() Marking Symbol

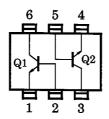
^{+0.2} 2.8 - 0.3 1.9 ± 0.2 2.9 ± 0.2 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 (B1) 4. EMITTER 2 5. BASE 2 (B2) SM6 6. COLLECTOR 1 **JEDEC** EIAJ **TOSHIBA** 2-3N1A Weight: 0.015g

Total rating

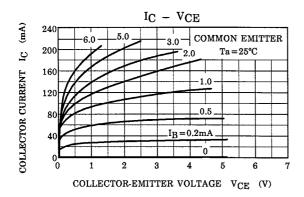
Marking

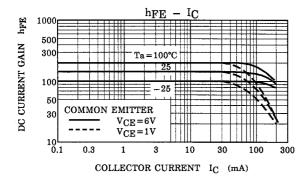
Equivalent Circuit (Top View)

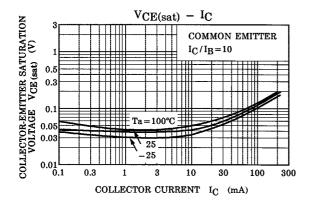


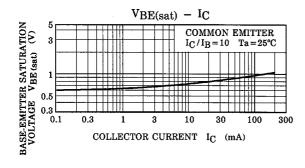


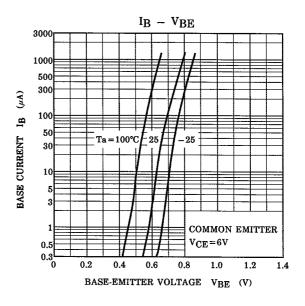
(Q1,Q2 Common)

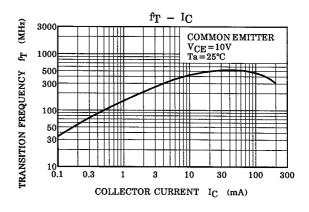


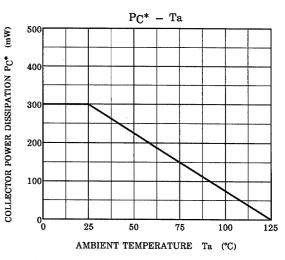












* : Total Rating

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